

ABSTRACT**Device, system and method for plasma-enhanced chemical
vapor deposition**

The present invention relates to a device (1), a system
(50) and a method (100) for plasma-enhanced chemical vapor
deposition. A process chamber (2) is configured to receive
at least one workpiece carrier (30). According to the in-
vention, the device (1) is configured to heat the process
chamber (2) with the aid of at least one workpiece carrier
(30) that can be received by the process chamber (2).

Fig. 1